

SESD3ZxxC

Transient Voltage Suppressors for ESD Protection

#### **General Description**

The SESD3ZxxC is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

#### Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

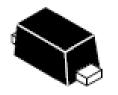
#### Features

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 350 Watts @ 8 x 20 µs Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Pb-Free package is available
  RoHS product for packing code suffix "G"
  Halogen free product for packing code suffix "H"

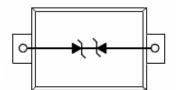
# Complies with the following standards IEC61000-4-2

Level 4 15 kV (air discharge) 8 kV(contact discharge) MIL STD 883E - Method 3015-7 Class 3 25 kV HBM (Human Body Model)

#### **Functional diagram**



SOD-323



Absolute	Absolute Ratings (T <sub>amb</sub> =25°C)						
Symbol	Parameter	Value	Units				
P <sub>PK</sub>	Peak Pulse Power ( $t_p = 8/20 \mu s$ )	350	W				
$T_{L}$	Maximum lead temperature for soldering during 10s	260	°C				
$T_{stg}$	Storage Temperature Range	-55 to +155	°C				
$T_{op}$	Operating Temperature Range	-40 to +125	°C				
TJ	Maximum junction temperature	150	°C				

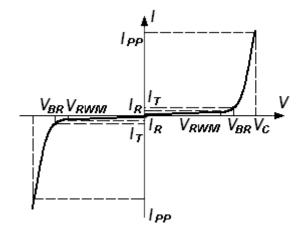


SESD3ZxxV

## Transient Voltage Suppressors for ESD Protection

#### **Electrical Parameter**

Symbol	Parameter	
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
V <sub>RWM</sub>	Working Peak Reverse Voltage	
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>	
Ι <sub>Τ</sub>	I <sub>T</sub> Test Current	
V <sub>BR</sub>	V <sub>BR</sub> Breakdown Voltage @ I <sub>T</sub>	



Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.							
		V <sub>BR</sub>					С
Part Numbers	Min.	Тур.	Max.	Ι <sub>Τ</sub>	V <sub>RWM</sub>	I <sub>R</sub>	Typ. (Note1)
	V	V	V	mA	V	μA	pF
SESD3Z5C	5.4	6.7	7.8	1	5.0	1	200
SESD3Z12C	13.3	14.5	15.7	1	12.0	1	100

1. Capacitance is measured at f=1MHz,  $V_R$ =0V,  $T_A$ =25°C.

### **Typical Characteristics**

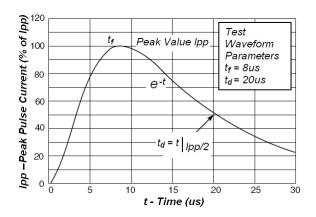


Fig1. Pulse Waveform

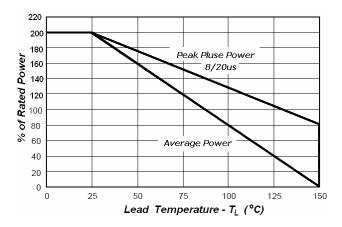


Fig2.Power Derating Curve



Transient Voltage Suppressors for ESD Protection

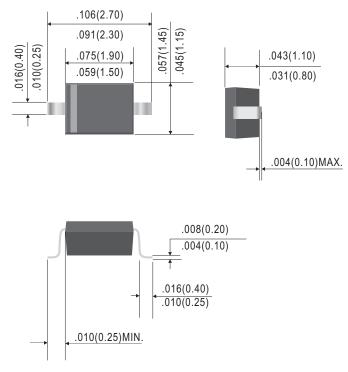
#### **Application Note**

Electrostatic discharge (ESD) is a major cause of failure in electronic systems. Transient Voltage Suppressors (TVS) are an ideal choice for ESD protection. They are capable of clamping the incoming transient to a low enough level such that damage to the protected semiconductor is prevented.

Surface mount TVS offers the best choice for minimal lead inductance. They serve as parallel protection elements, connected between the signal lines to ground. As the transient rises above the operating voltage of the device, the TVS becomes a low impedance path diverting the transient current to ground. The SESD3ZxxC is the ideal board evel protection of ESD sensitive semiconductor components.

The tiny SOD-323 package allows design flexibility in the design of high density boards where the space saving is at a premium. This enables to shorten the routing and contributes to hardening against ESD.

#### SOD-323 Mechanical Data



Dimensions in inches and (millimeters)

#### Marking

Typenumber	Marking code		
SESD3Z5C	CC		
SESD3Z12C	12C		

SESD3ZxxV